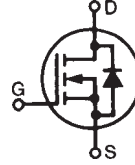


Polar™ HiperFET™ Power MOSFET

IXFK170N20P
IXFX170N20P

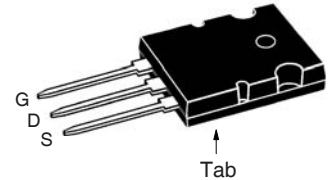
V_{DSS} = 200V
I_{D25} = 170A
R_{DS(on)} ≤ 14mΩ

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

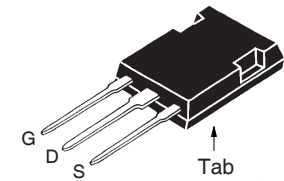


| Symbol | Test Conditions | Maximum Ratings | |
|-------------------|--|----------------------------|------------------|
| V _{DSS} | T _J = 25°C to 175°C | 200 | V |
| V _{DGR} | T _J = 25°C to 175°C, R _{GS} = 1MΩ | 200 | V |
| V _{GSS} | Continuous | ±20 | V |
| V _{GSM} | Transient | ±30 | V |
| I _{D25} | T _C = 25°C | 170 | A |
| I _{LRMS} | Lead Current Limit | 160 | A |
| I _{DM} | T _C = 25°C, Pulse Width Limited by T _{JM} | 400 | A |
| I _A | T _C = 25°C | 85 | A |
| E _{AS} | T _C = 25°C | 4 | J |
| dv/dt | I _S ≤ I _{DM} , V _{DD} ≤ V _{DSS} , T _J ≤ 175°C | 20 | V/ns |
| P _D | T _C = 25°C | 1250 | W |
| T _J | | -55 ... +175 | °C |
| T _{JM} | | 175 | °C |
| T _{stg} | | -55 ... +175 | °C |
| L | Maximum Lead Temperature for Soldering | 300 | °C |
| T _{SOLD} | 1.6 mm (0.062in.) from Case for 10s | 260 | °C |
| M _d | Mounting Force (PLUS247) Mounting Torque (TO-264) | 20..120/4.5..27 1.13/10 | N/lb Nm/lb.in |
| Weight | PLUS247 TO-264 | 6 10 | g g |

TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate D = Drain
S = Source Tab = Drain

Features

- Dynamic dv/dt Rating
- Avalanche Rated
- Fast Intrinsic Diode
- Low Q_G
- Low R_{DS(on)}
- Low Drain-to-Tab Capacitance
- Low Package Inductance

Advantages

- Easy to Mount
- Space Savings

Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- Uninterrupted Power Supplies
- AC Motor Drives
- DC Choppers
- High Speed Power Switching Applications

| Symbol | Test Conditions (T _J = 25°C, Unless Otherwise Specified) | Characteristic Values | | |
|---------------------|---|-----------------------|------|---------------|
| | | Min. | Typ. | Max. |
| BV _{DSS} | V _{GS} = 0V, I _D = 3mA | 200 | | V |
| V _{GS(th)} | V _{DS} = V _{GS} , I _D = 1mA | 2.5 | | 4.5 V |
| I _{GSS} | V _{GS} = ±20V, V _{DS} = 0V | | | ±200 nA |
| I _{DSS} | V _{DS} = V _{DSS} , V _{GS} = 0V T _J = 150°C | | | 50 μA 1 mA |
| R _{DS(on)} | V _{GS} = 10V, I _D = 0.5 • I _{D25} , Note 1 | | | 14 mΩ |

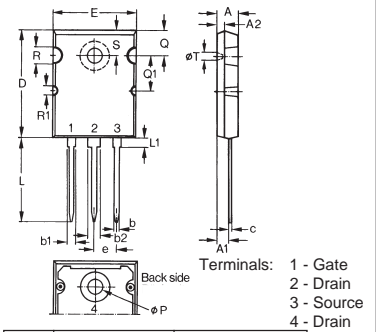
| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|--|-----------------------|------|--------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 10\text{V}, I_D = 60\text{A}$, Note 1 | 45 | 75 | S |
| C_{iss} | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$ | | 11.4 | nF |
| C_{oss} | | | 2440 | pF |
| C_{rss} | | | 70 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External) | | 40 | ns |
| t_r | | | 25 | ns |
| $t_{d(off)}$ | | | 50 | ns |
| t_f | | | 14 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ | | 185 | nC |
| Q_{gs} | | | 80 | nC |
| Q_{gd} | | | 60 | nC |
| R_{thJC} | | | 0.12 | $^\circ\text{C/W}$ |
| R_{thCS} | | 0.15 | | $^\circ\text{C/W}$ |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|----------|---|-----------------------|------|---------------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{V}$ | | | 170 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 510 A |
| V_{SD} | $I_F = 85\text{A}, V_{GS} = 0\text{V}$, Note 1 | | | 1.3 V |
| t_{rr} | $I_F = 85\text{A}, -di/dt = 150\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$ | | 1.6 | 200 ns |
| Q_{RM} | | | 20 | μC |
| I_{RM} | | | | A |

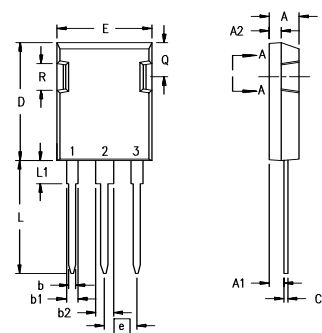
Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

TO-264 AA Outline



| Dim. | Millimeter | | Inches | |
|------|------------|-------|----------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.82 | 5.13 | .190 | .202 |
| A1 | 2.54 | 2.89 | .100 | .114 |
| A2 | 2.00 | 2.10 | .079 | .083 |
| b | 1.12 | 1.42 | .044 | .056 |
| b1 | 2.39 | 2.69 | .094 | .106 |
| b2 | 2.90 | 3.09 | .114 | .122 |
| c | 0.53 | 0.83 | .021 | .033 |
| D | 25.91 | 26.16 | 1.020 | 1.030 |
| E | 19.81 | 19.96 | .780 | .786 |
| e | 5.46 BSC | | .215 BSC | |
| J | 0.00 | 0.25 | .000 | .010 |
| K | 0.00 | 0.25 | .000 | .010 |
| L | 20.32 | 20.83 | .800 | .820 |
| L1 | 2.29 | 2.59 | .090 | .102 |
| P | 3.17 | 3.66 | .125 | .144 |
| Q | 6.07 | 6.27 | .239 | .247 |
| Q1 | 8.38 | 8.69 | .330 | .342 |
| R | 3.81 | 4.32 | .150 | .170 |
| R1 | 1.78 | 2.29 | .070 | .090 |
| S | 6.04 | 6.30 | .238 | .248 |
| T | 1.57 | 1.83 | .062 | .072 |

PLUS247™ Outline



Terminals: 1 - Gate
2 - Drain
3 - Source

| Dim. | Millimeter | | Inches | |
|------|------------|-------|----------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.83 | 5.21 | .190 | .205 |
| A1 | 2.29 | 2.54 | .090 | .100 |
| A2 | 1.91 | 2.16 | .075 | .085 |
| b | 1.14 | 1.40 | .045 | .055 |
| b1 | 1.91 | 2.13 | .075 | .084 |
| b2 | 2.92 | 3.12 | .115 | .123 |
| C | 0.61 | 0.80 | .024 | .031 |
| D | 20.80 | 21.34 | .819 | .840 |
| E | 15.75 | 16.13 | .620 | .635 |
| e | 5.45 BSC | | .215 BSC | |
| L | 19.81 | 20.32 | .780 | .800 |
| L1 | 3.81 | 4.32 | .150 | .170 |
| Q | 5.59 | 6.20 | .220 | 0.244 |
| R | 4.32 | 4.83 | .170 | .190 |

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

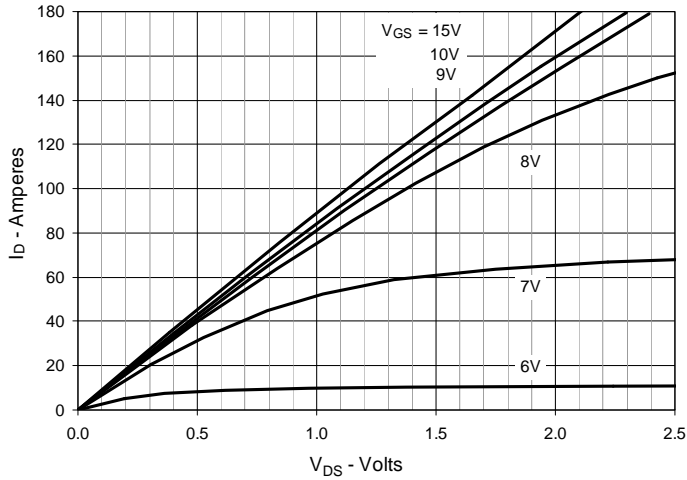


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

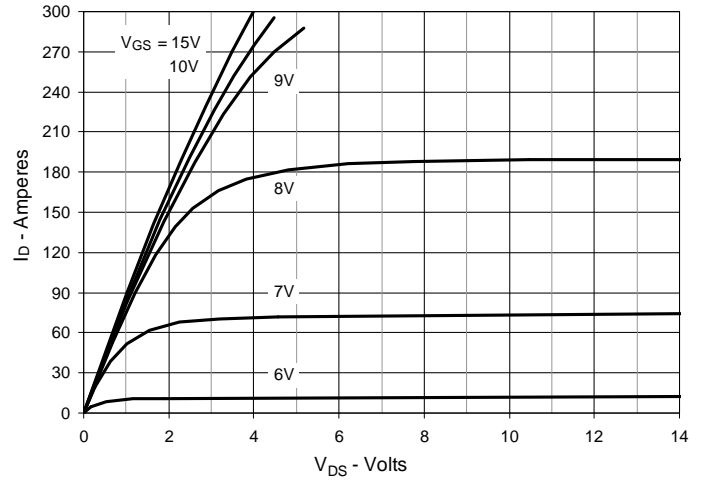


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

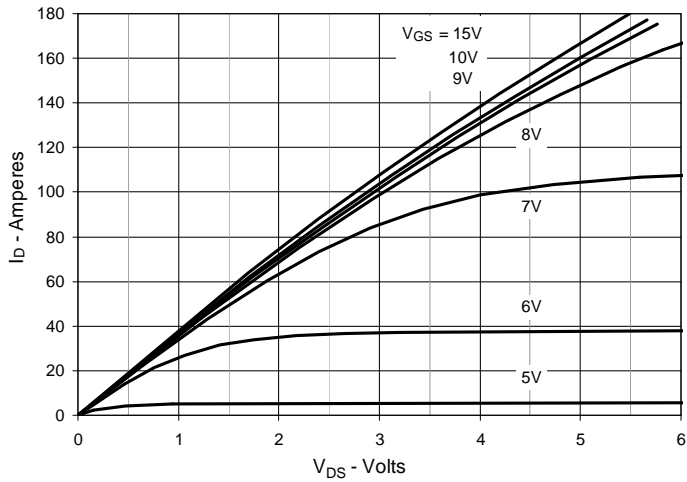


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 85\text{A}$ Value vs. Junction Temperature

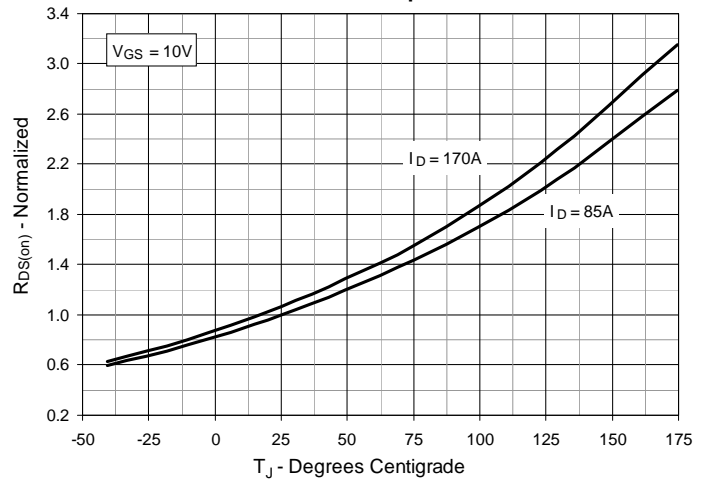


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 85\text{A}$ Value vs. Drain Current

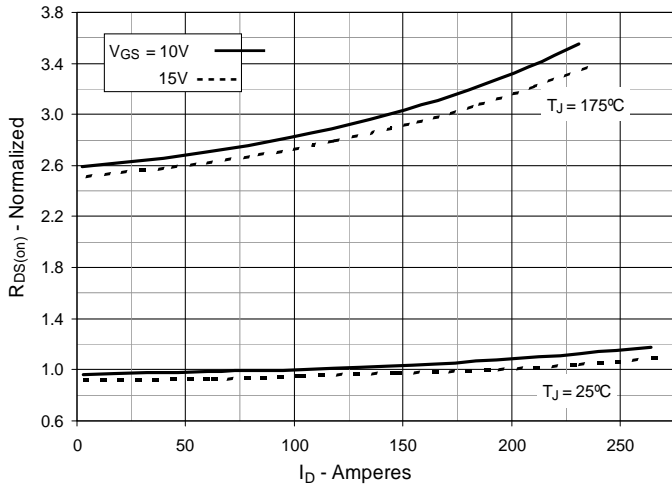


Fig. 6. Maximum Drain Current vs. Case Temperature

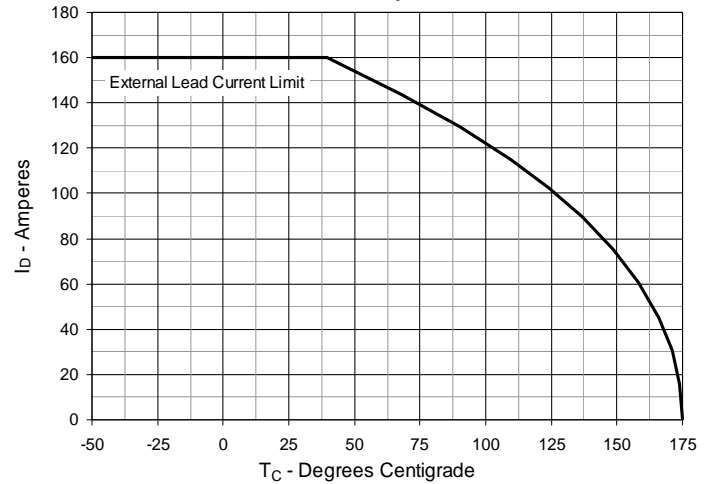


Fig. 7. Input Admittance

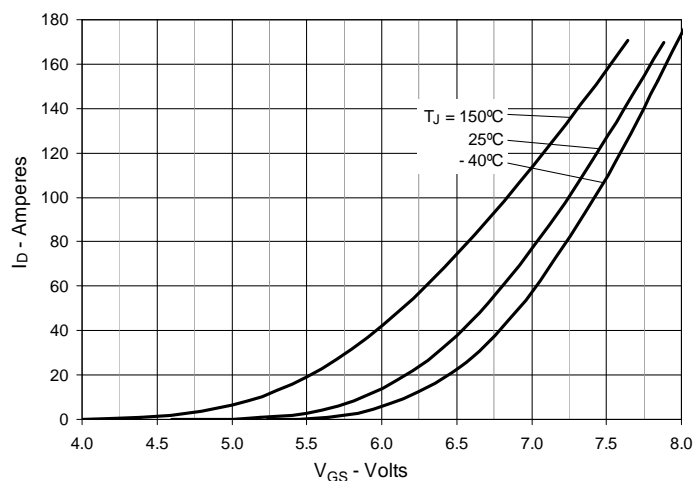


Fig. 8. Transconductance

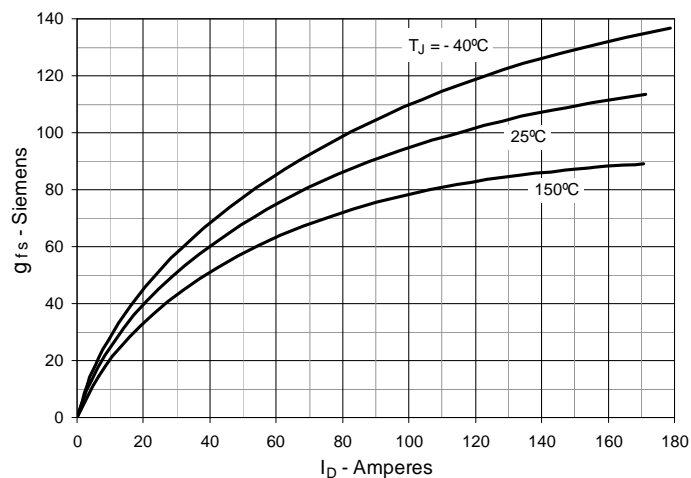


Fig. 9. Forward Voltage Drop of Intrinsic Diode

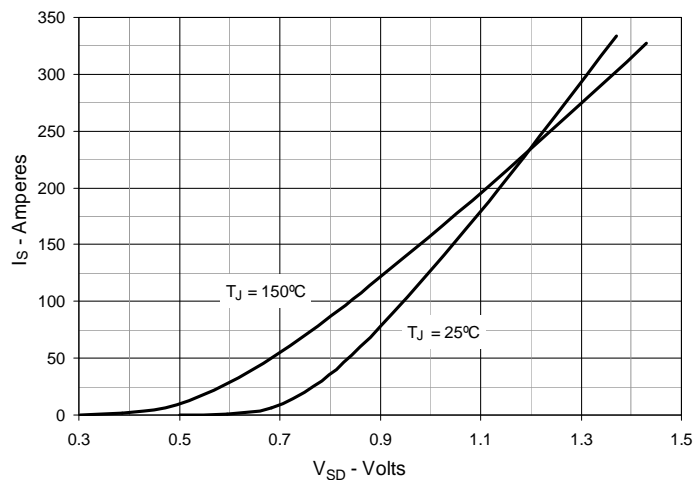


Fig. 10. Gate Charge

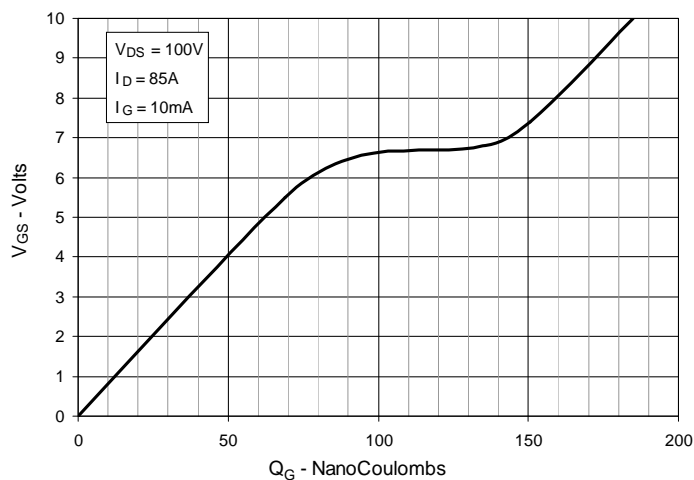


Fig. 11. Capacitance

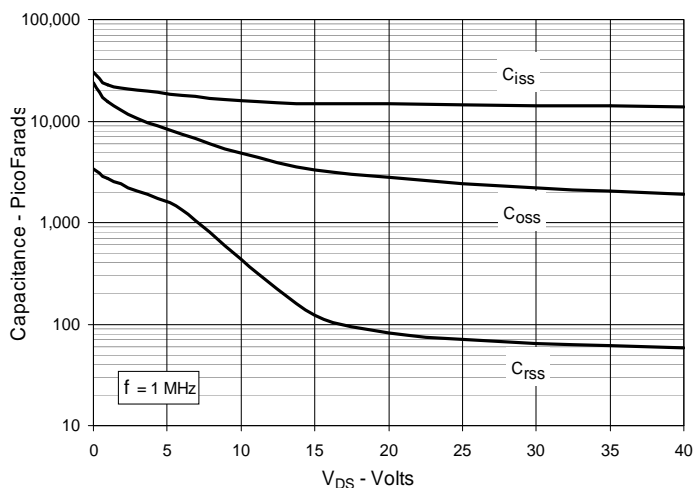


Fig. 12. Forward-Bias Safe Operating Area

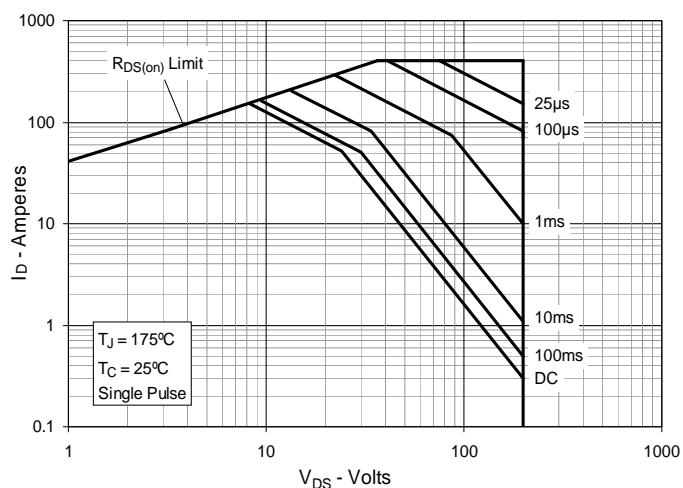
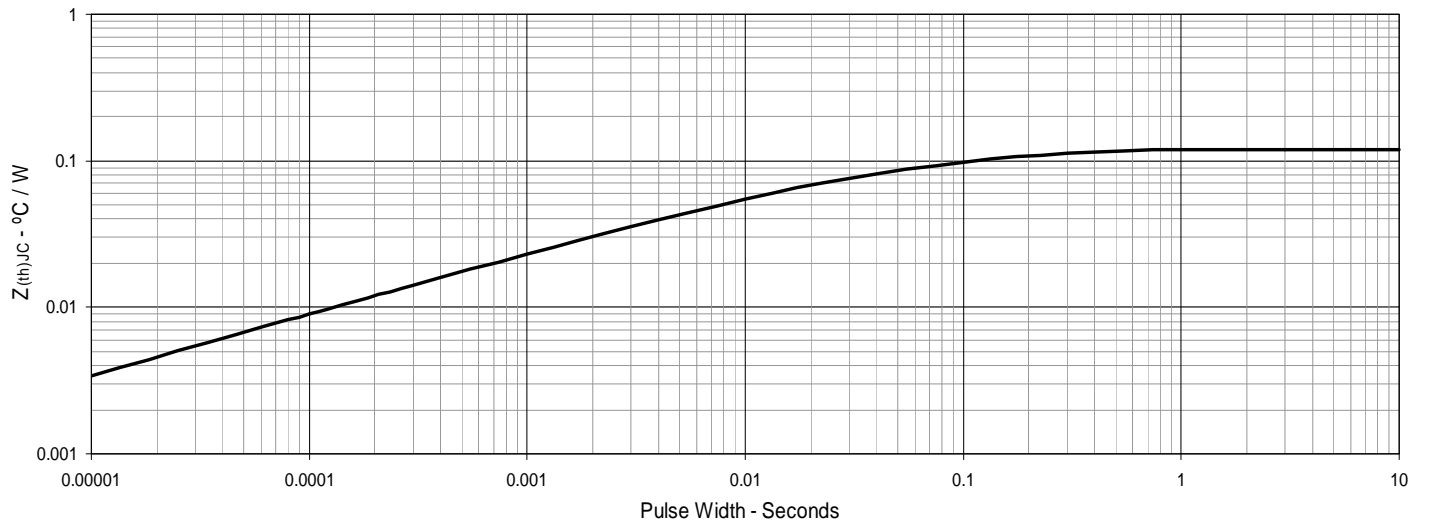


Fig. 13. Maximum Transient Thermal Impedance





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